

Title (en)

PROCESS FOR MANUFACTURING AN ACTIVE MATRIX DISPLAY.

Title (de)

HERSTELLUNGSVERFAHREN FÜR AKTIVMATRIX-BILDSCHIRM.

Title (fr)

PROCEDE DE FABRICATION D'UN AFFICHAGE A MATRICE ACTIVE.

Publication

**EP 0647354 A4 19950830 (EN)**

Application

**EP 93910769 A 19930426**

Priority

- DE 4310640 A 19930331
- US 9303854 W 19930426

Abstract (en)

[origin: DE4310640C1] The mfg. system for a Si:H thin-film transistors with storage capacitors uses 2 sputtered and structured chrome surfaces (11,12) applied to a substrate (10), respectively providing a row line nad a gate contact for each thin film transistor (19) and the base electrode of the storage capacitor. A gate isolator (13) and a Si:H intrinsic and doped semiconductor layers (14,15) are then applied, with wet or dry etching of the semiconductor layers via a metallisation mask. An indium-tin oxide is deposited and structured to form image print electrodes with a further metallisation for the matrix columns and etching of the metallisation mask using the indium-tin oxide as the mask. A transparent passivation layer is then applied. USE - For simplified mfr. of liquid crystal display screen.

IPC 1-7

**H01L 21/336**; **H01L 21/84**; **H01L 29/772**

IPC 8 full level

**H01L 21/77** (2006.01); **H01L 21/84** (2006.01)

CPC (source: EP US)

**H01L 27/1214** (2013.01 - EP); **H01L 27/1288** (2013.01 - EP US)

Citation (search report)

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- [XY] PATENT ABSTRACTS OF JAPAN vol. 017, no. 344 (E - 1390) 29 June 1993 (1993-06-29)
- See references of WO 9423446A1

Designated contracting state (EPC)

FR GB NL

DOCDB simple family (publication)

**DE 4310640 C1 19940511**; EP 0647354 A1 19950412; EP 0647354 A4 19950830; WO 9423446 A1 19941013

DOCDB simple family (application)

**DE 4310640 A 19930331**; EP 93910769 A 19930426; US 9303854 W 19930426